

# Power MOSFET

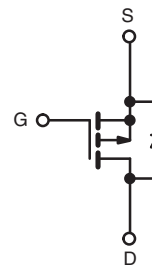
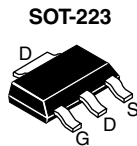
PRODUCT SUMMARY		
$V_{DS}$ (V)	-250	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = -10\text{ V}$	1.2
$Q_g$ (Max.) (nC)	8.7	
$Q_{gs}$ (nC)	2.2	
$Q_{gd}$ (nC)	4.1	
Configuration	Single	

## FEATURES

- Surface mount
- Available in tape and reel
- Dynamic dV/dt rating
- Repetitive avalanche rated
- P-channel
- Fast switching
- Ease of paralleling



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P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)				
PARAMETER	SYMBOL		LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$		-250	V
Gate-Source Voltage	$V_{GS}$		$\pm 20$	
Continuous Drain Current	$V_{GS}$ at -10 V	$T_C = 25\text{ }^\circ\text{C}$	-2.1	A
		$T_C = 100\text{ }^\circ\text{C}$	-1.69	
Pulsed Drain Current <sup>a</sup>	$I_{DM}$		-8.8	
Linear Derating Factor			0.025	W/ $^\circ\text{C}$
Linear Derating Factor (PCB Mount) <sup>e</sup>			0.017	
Single Pulse Avalanche Energy <sup>b</sup>	$E_{AS}$		100	mJ
Avalanche Current <sup>a</sup>	$I_{AR}$		-1.1	A
Repetitive Avalanche Energy <sup>a</sup>	$E_{AR}$		0.31	mJ
Maximum Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$		3.1	W
	$T_A = 25\text{ }^\circ\text{C}$		2.0	
Peak Diode Recovery dV/dt <sup>c</sup>	dV/dt		-5.5	V/ns
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$		-55 to +150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature) <sup>d</sup>	for 10 s		300	

### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = -25\text{ V}$ , starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 7.7\text{ mH}$ ,  $R_g = 25\text{ }\Omega$ ,  $I_{AS} = -4.4\text{ A}$  (see fig. 12).
- $I_{SD} \leq -4.4\text{ A}$ ,  $dI/dt \leq -75\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150\text{ }^\circ\text{C}$ .
- 1.6 mm from case.
- When mounted on 1" square PCB (FR-4 or G-10 material).

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient (PCB Mount) <sup>a</sup>	R <sub>thJA</sub>	-	-	60	°C/W
Maximum Junction-to-Case (Drain)	R <sub>thJC</sub>	-	-	40	

**Note**

a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA		-250	-	-	V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	Reference to 25 °C, I <sub>D</sub> = -1 mA		-	-0.091	-	V/°C
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA		-2.0	-	-4.0	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -100 V, V <sub>GS</sub> = 0 V		-	-	-100	μA
		V <sub>DS</sub> = -80 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C		-	-	- 500	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -0.66 A <sup>b</sup>	-	1.2	-	Ω
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> = -50 V, I <sub>D</sub> = -0.66 A		0.82	-	-	S
<b>Dynamic</b>							
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = - 25 V, f = 1.0 MHz, see fig. 5		-	200	-	pF
Output Capacitance	C <sub>oss</sub>			-	94	-	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	18	-	
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -4.0 A, V <sub>DS</sub> = -80 V, see fig. 6 and 13 <sup>b</sup>	-	-	8.7	nC
Gate-Source Charge	Q <sub>gs</sub>			-	-	2.2	
Gate-Drain Charge	Q <sub>gd</sub>			-	-	4.1	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = -50 V, I <sub>D</sub> = -4.0 A, R <sub>G</sub> = 24 Ω, R <sub>D</sub> = 11 Ω, see fig. 10 <sup>b</sup>		-	10	-	ns
Rise Time	t <sub>r</sub>			-	27	-	
Turn-Off Delay Time	t <sub>d(off)</sub>			-	15	-	
Fall Time	t <sub>f</sub>			-	17	-	
Internal Drain Inductance	L <sub>D</sub>	Between lead, 6 mm (0.25") from package and center of die contact		-	4.0	-	nH
Internal Source Inductance	L <sub>S</sub>			-	6.0	-	
<b>Drain-Source Body Diode Characteristics</b>							
Continuous Source-Drain Diode Current	I <sub>S</sub>	MOSFET symbol showing the integral reverse p - n junction diode		-	-	-1.1	A
Pulsed Diode Forward Current <sup>a</sup>	I <sub>SM</sub>			-	-	-8.8	
Body Diode Voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C, I <sub>S</sub> = -1.1 A, V <sub>GS</sub> = 0 V <sup>b</sup>		-	-	-5.5	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C, I <sub>F</sub> = -4.0 A, di/dt = 100 A/μs <sup>b</sup>		-	80	160	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			-	0.15	0.30	μC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> and L <sub>D</sub> )					

**Notes**

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).

b. Pulse width ≤ 300 μs; duty cycle ≤ 2 %.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

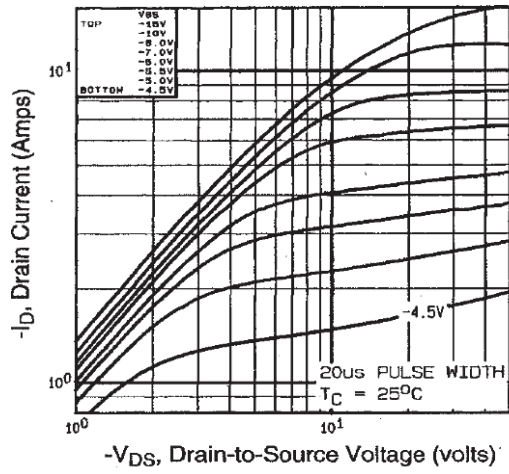


Fig. 1 - Typical Output Characteristics

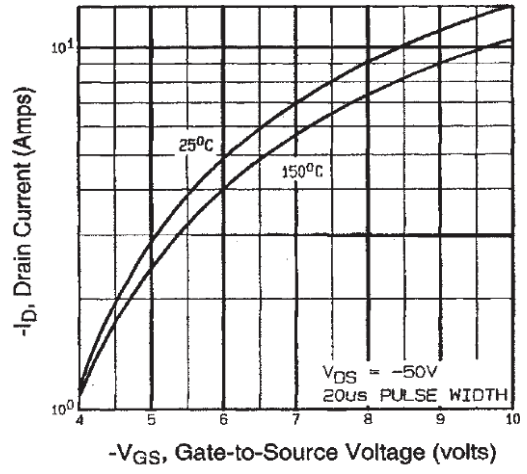


Fig. 3 - Typical Transfer Characteristics

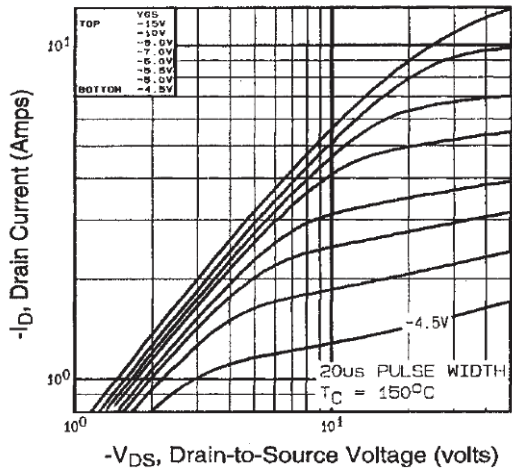


Fig. 2 - Typical Output Characteristics

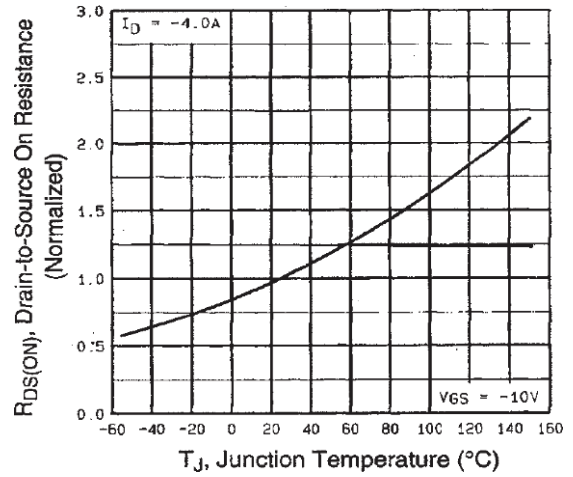


Fig. 4 - Normalized On-Resistance vs. Temperature

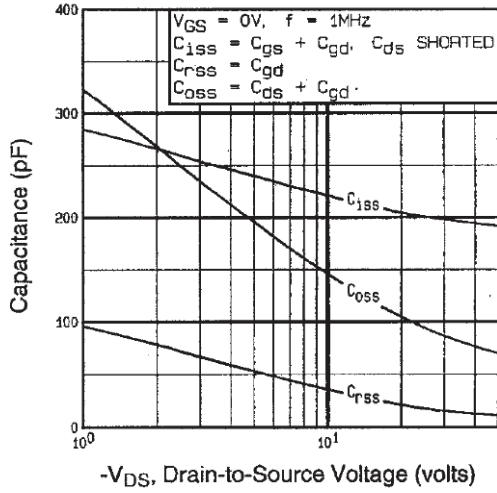


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

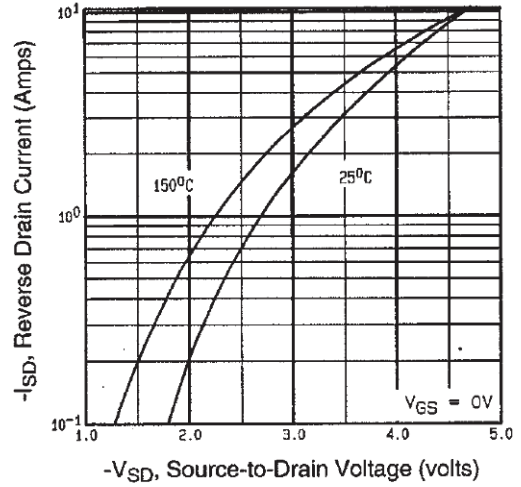


Fig. 7 - Typical Source-Drain Diode Forward Voltage

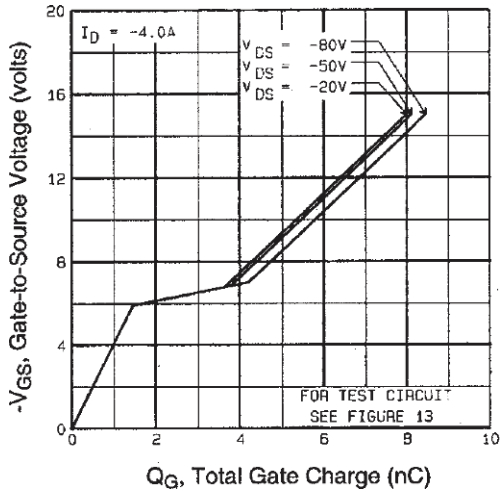


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

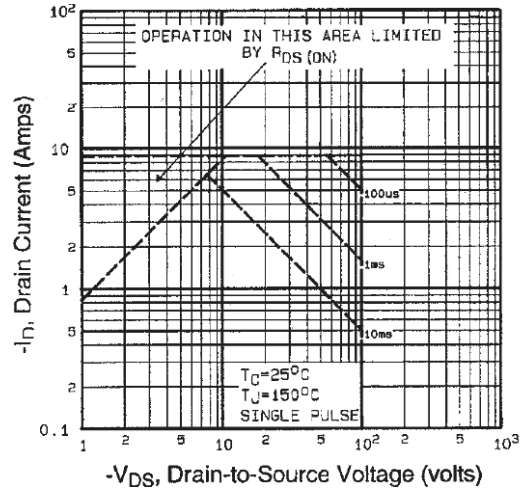


Fig. 8 - Maximum Safe Operating Area

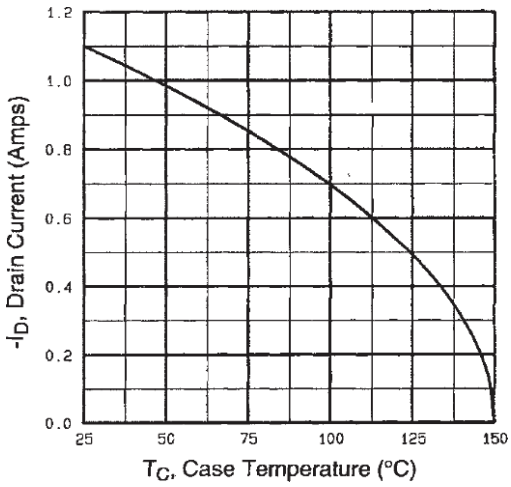


Fig. 9 - Maximum Drain Current vs. Case Temperature

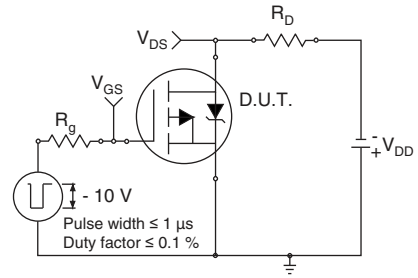


Fig. 10a - Switching Time Test Circuit

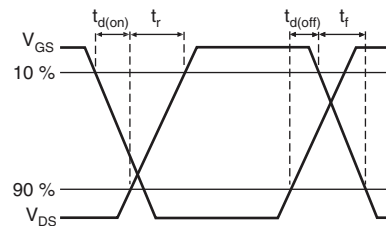


Fig. 10b - Switching Time Waveforms

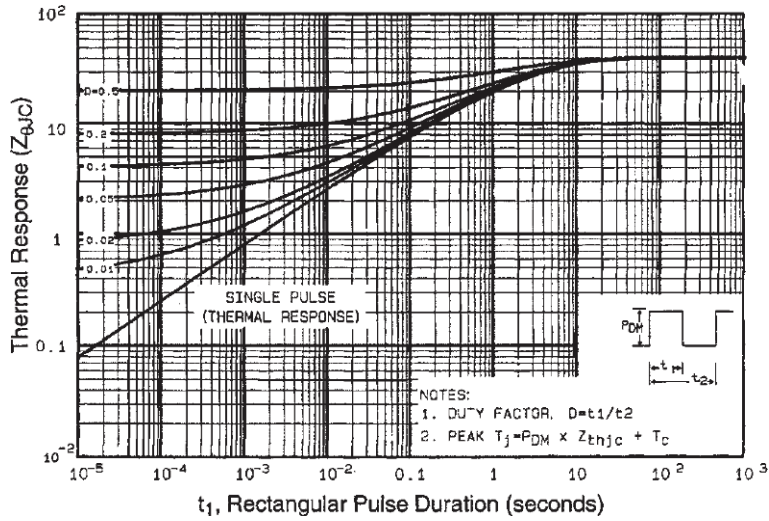


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

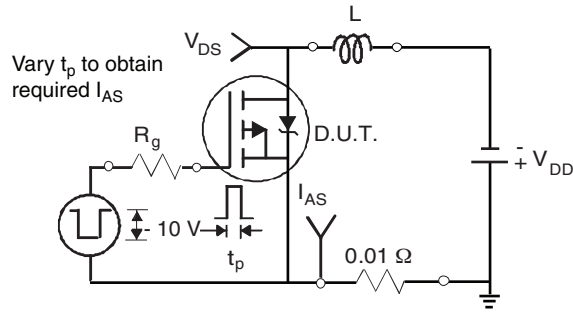


Fig. 12a - Unclamped Inductive Test Circuit

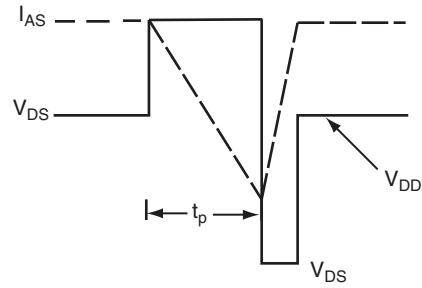


Fig. 12b - Unclamped Inductive Waveforms

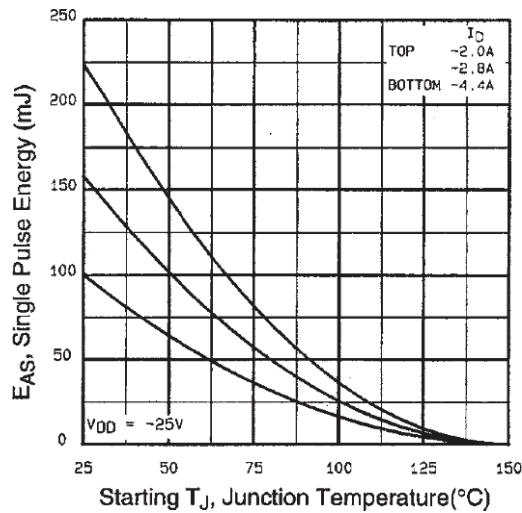


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

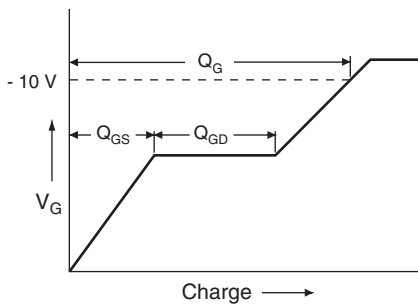


Fig. 13a - Basic Gate Charge Waveform

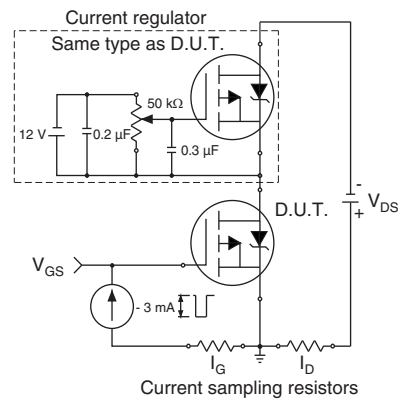
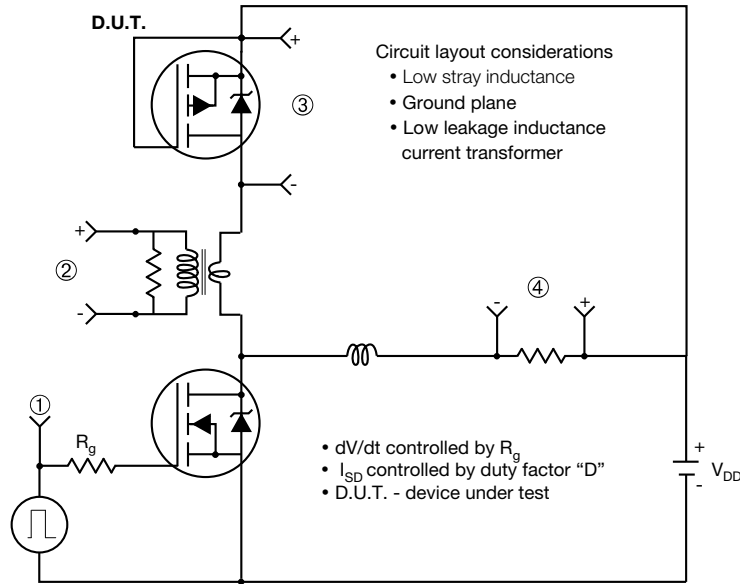
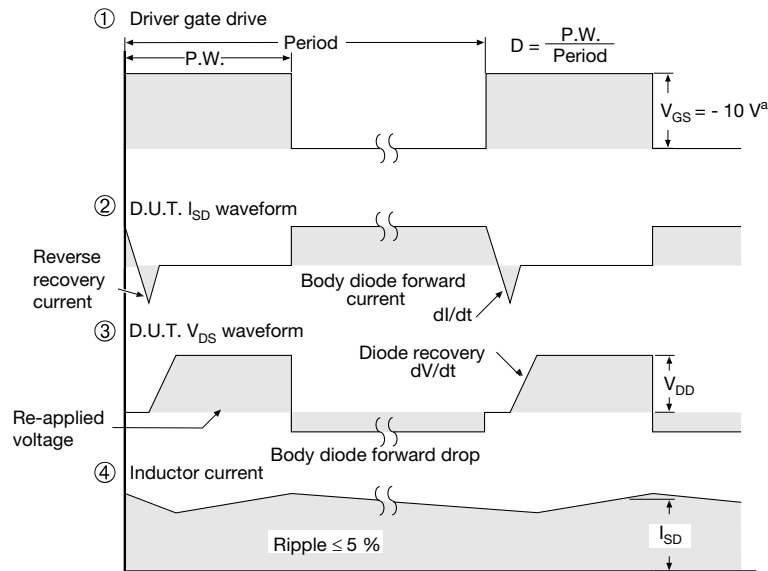


Fig. 13b - Gate Charge Test Circuit

**Peak Diode Recovery dV/dt Test Circuit**

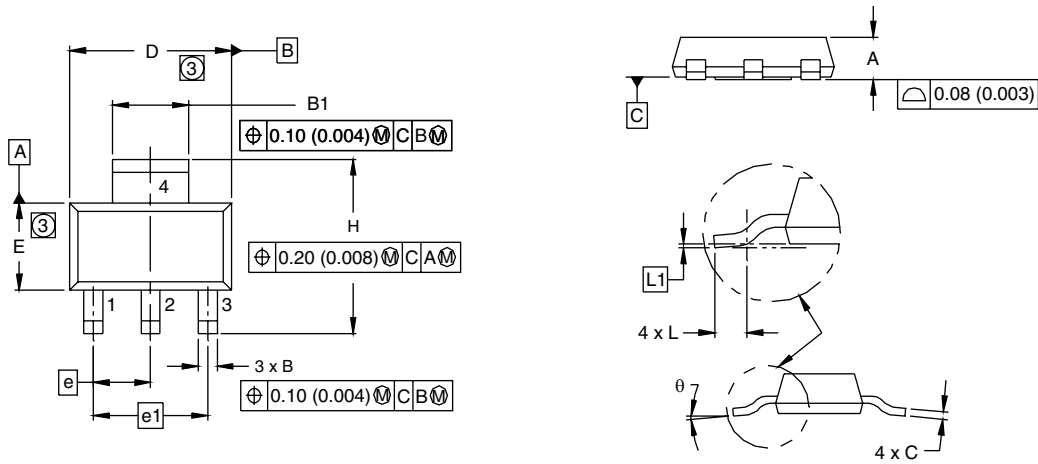


**Note**  
• Compliment N-Channel of D.U.T. for driver



**Fig. 14 - For P-Channel**

**SOT-223 (HIGH VOLTAGE)**



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	1.55	1.80	0.061	0.071
B	0.65	0.85	0.026	0.033
B1	2.95	3.15	0.116	0.124
C	0.25	0.35	0.010	0.014
D	6.30	6.70	0.248	0.264
E	3.30	3.70	0.130	0.146
e	2.30 BSC		0.0905 BSC	
e1	4.60 BSC		0.181 BSC	
H	6.71	7.29	0.264	0.287
L	0.91	-	0.036	-
L1	0.061 BSC		0.0024 BSC	
$\theta$	-	10'	-	10'
ECN: S-82109-Rev. A, 15-Sep-08 DWG: 5969				

**Notes**

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension do not include mold flash.
4. Outline conforms to JEDEC outline TO-261AA.



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